

AMENDMENTS TO THE SPECIFICATION:

Page 4, replace the paragraph, beginning on line 8, with the following amended paragraph:

--However, the high-k film generally involves a problem of having lower thermal resistance, and thus when a high-k film is formed directly on the silicon substrate, a chemical reaction between the high-k film and the surface of the silicon substrate during [[a]] thermal processing ~~to deteriorate~~ causes the device properties to deteriorate ~~will occur~~. Therefore, it is proposed to provide a silicon oxide film between the high-k film and the silicon substrate to inhibit such deterioration of the device properties (see, for example, JP-A-2001-274,378). In this case, the thickness of the formed silicon oxide film is preferably controlled to have ~~thinner~~ as thin a film thickness as possible, in order to maintain the driving capacity of the gate.--